4V Drive Pch MOSFET

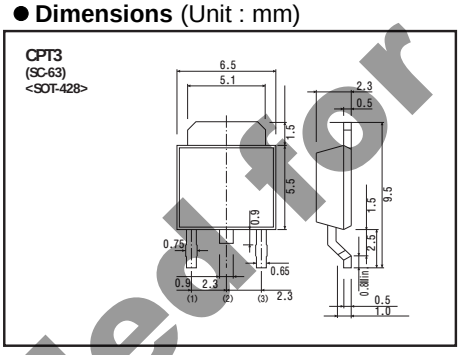
RSD080P05

●Structure
Silicon P-channel MOSFET

●Features
1) Low on-resistance.
2) Fast switching speed.
3) Drive circuits can be simple.
4) Parallel use is easy.

● Application
Switching

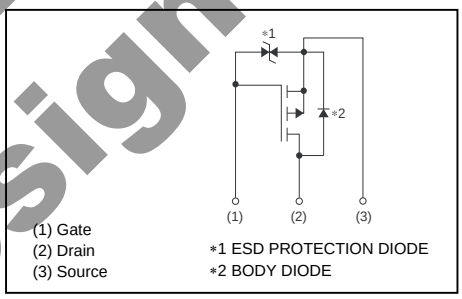
● Dimensions (Unit : mm)



● Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	2500
RSD080P05		O

● Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	−45	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±8.0	A
	Pulsed	I_{DP} *1	±16	A
Source current (Body Diode)	Continuous	I_S	−8.0	A
	Pulsed	I_{SP} *1	−16	A
Power dissipation		P_D *2	15	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≦10μs, Duty cycle≦1%
*2 T_c=25°C

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th\ (ch\text{-}c)}$ *	8.33	°C / W

* T_c=25°C

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● **Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	−45	-	-	V	I_D=−1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	−1	μA	V_{DS}=−45V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	−1.0	-	−3.0	V	V_{DS}=−10V, I_D=−1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	-	65	91	mΩ	I_D=−8.0A, V_{GS}=−10V
		-	95	133		I_D=−8.0A, V_{GS}=−4.5V
		-	105	147		I_D=−8.0A, V_{GS}=−4.0V
Forward transfer admittance	$\|Y_{fs}\|$*	6.0	-	-	S	I_D=−8.0A, V_{DS}=−10V
Input capacitance	C_{iss}	-	1000	-	pF	V_{DS}=−10V
Output capacitance	C_{oss}	-	160	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	80	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$*	-	12	-	ns	I_D=−4.0A, V_{DD}≒−25V
Rise time	t_r *	-	15	-	ns	V_{GS}=−10V
Turn-off delay time	$t_{d(off)}$*	-	50	-	ns	R_L=6.25Ω
Fall time	t_f *	-	20	-	ns	R_G=10Ω
Total gate charge	Q_g *	-	9.0	-	nC	V_{DD}≒−25V
Gate-source charge	Q_{gs} *	-	4.0	-	nC	I_D=−8.0A,
Gate-drain charge	Q_{gd} *	-	3.0	-	nC	V_{GS}=−5V

*Pulsed

●**Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}*	-	-	−1.2	V	I_s=−8.0A, V_{GS}=0V

*Pulsed

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●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (Ⅰ)

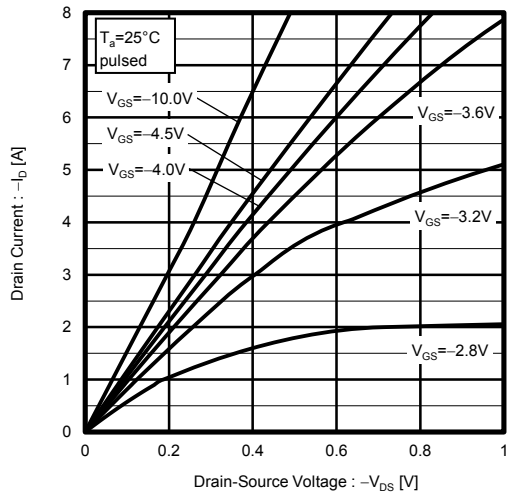


Fig.2 Typical Output Characteristics (Ⅱ)

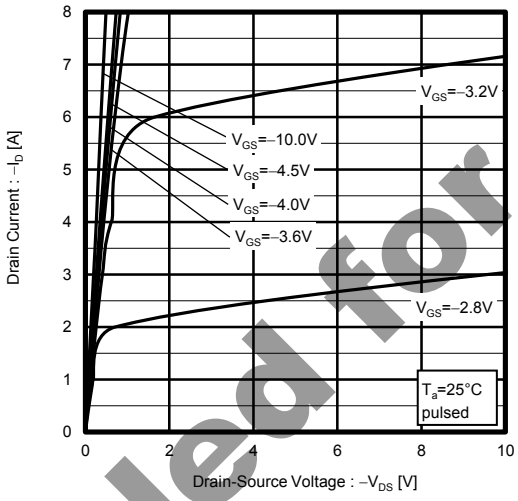


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

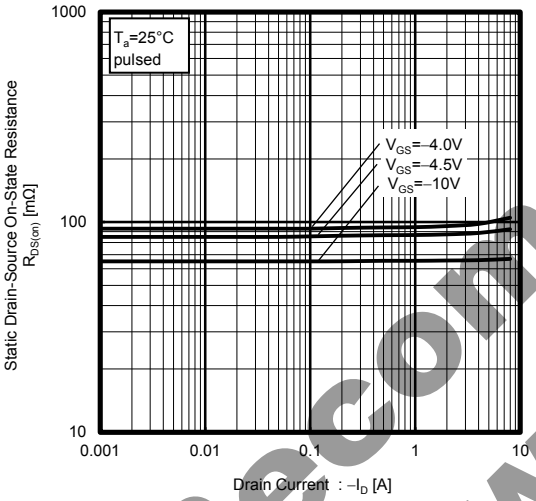


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

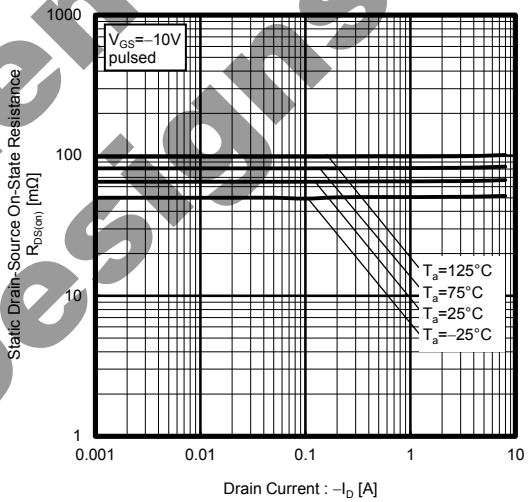


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

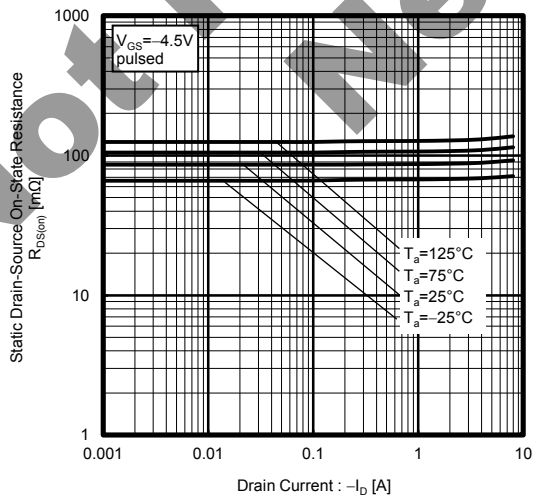
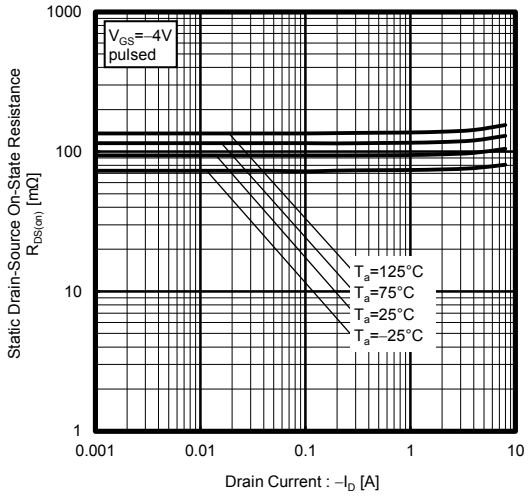


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current



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Fig.7 Forward Transfer Admittance vs. Drain Current

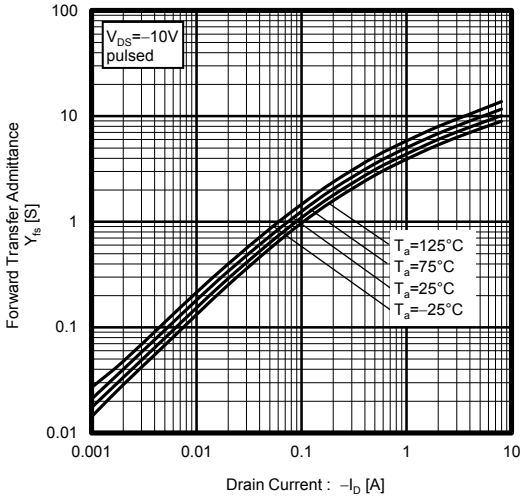


Fig.8 Typical Transfer Characteristics

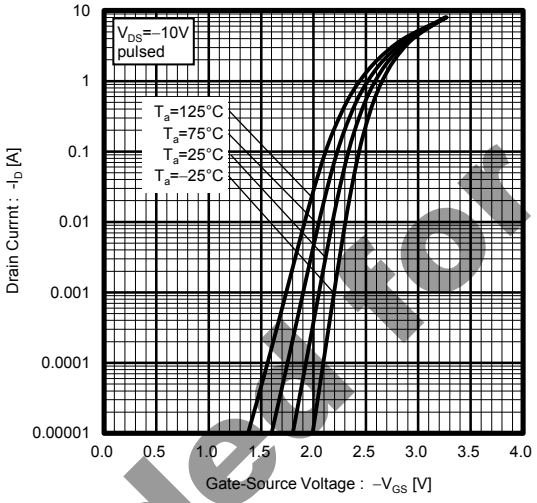


Fig.9 Source Current vs. Source-Drain Voltage

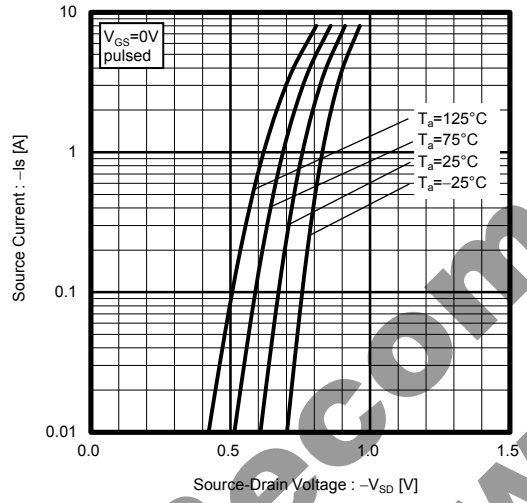


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

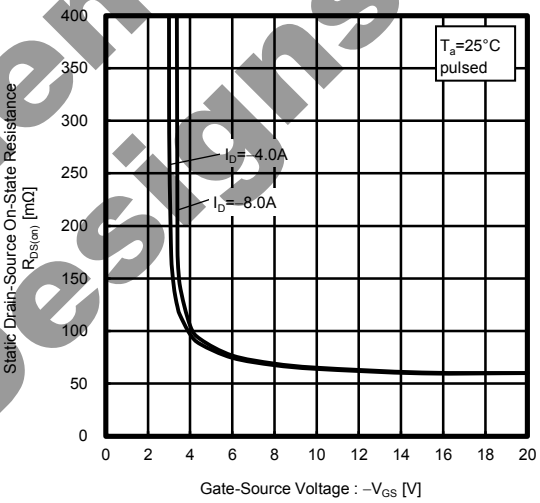


Fig.11 Switching Characteristics

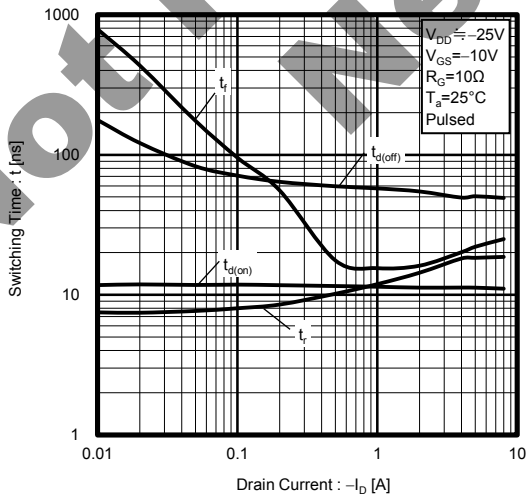
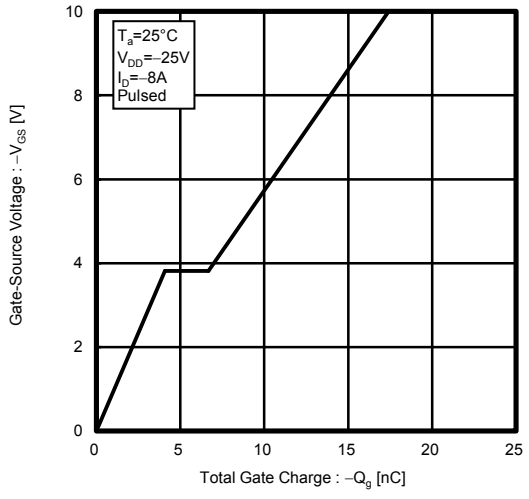


Fig.12 Dynamic Input Characteristics



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Fig.13 Typical Capacitance vs. Drain-Source Voltage

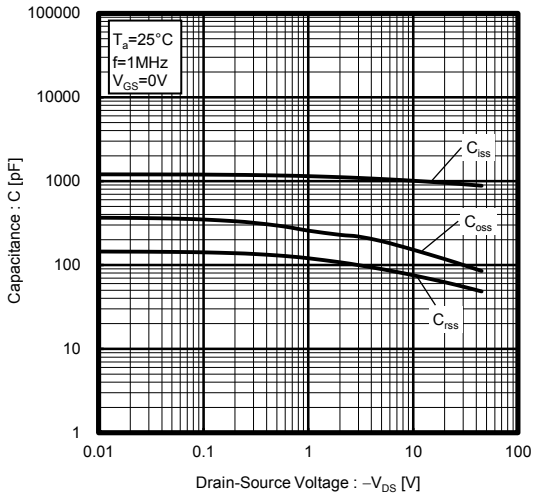


Fig.14 Maximum Safe Operating Area

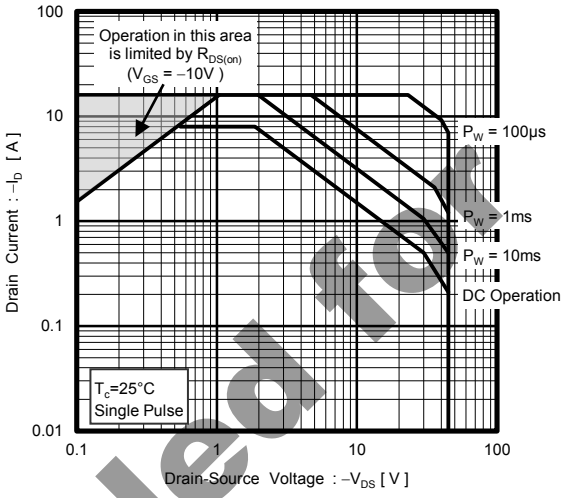
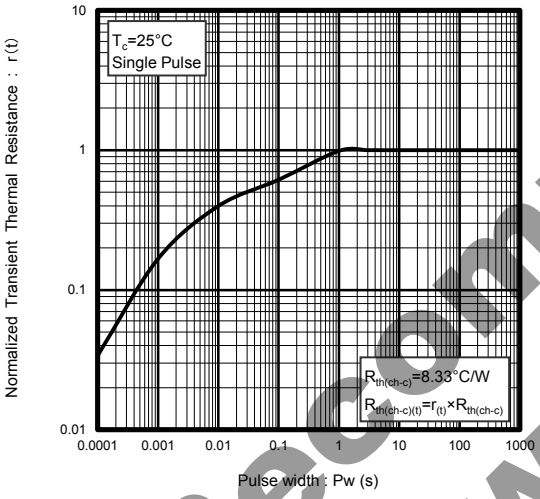


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



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● **Measurement circuits**

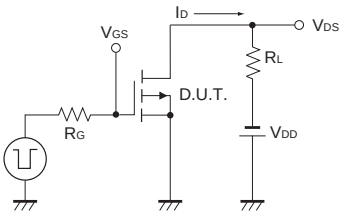


Fig.1-1 Switching Time Measurement Circuit

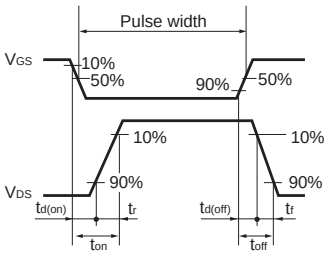


Fig.1-2 Switching Waveforms

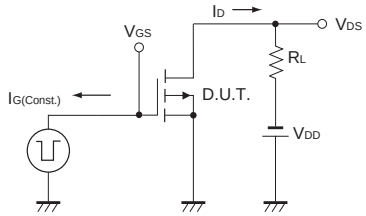


Fig.2-1 Gate Charge Measurement Circuit

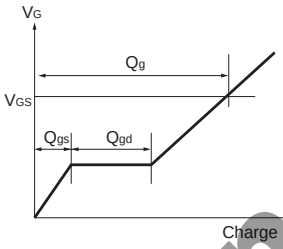


Fig.2-2 Gate Charge Waveform

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